

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
30V	6.1mΩ@10V	60A
	14mΩ@4.5V	

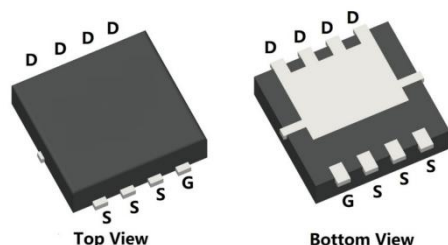
Feature

- Trench Power LV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$
- Epoxy Meets UL 94 V-0 Flammability Rating
- Suffix “-Q1” for AEC-Q101

Application

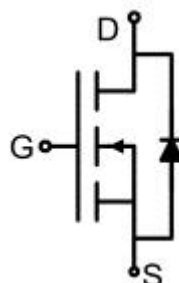
- Power switching application
- Uninterruptible power supply
- DC-DC convertor

Package

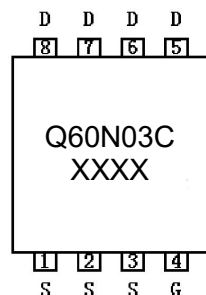


PDFN3.3*3.3-8L

Circuit diagram



Marking



Absolute maximum ratings ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($T_C=25^{\circ}\text{C}$)	I_D	60	A
Continuous Drain Current ($T_C=100^{\circ}\text{C}$)	$I_D(100^{\circ}\text{C})$	38	A
Pulsed Drain Current ¹⁾	I_{DM}	200	A
Power Dissipation ³⁾ ($T_C=25^{\circ}\text{C}$)	P_D	39	W
Single pulse avalanche energy ²⁾	E_{AS}	70.8	mJ
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.2	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Electrical characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D =250μA	30			V
Zero gate voltage drain current	I _{DSS}	V _{DS} =30V,V _{GS} = 0V			1	μA
Gate-body leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V			±100	nA
Gate threshold voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.1	1.5	2.2	V
Drain-source on-resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A		4.7	6.1	mΩ
		V _{GS} =4.5V, I _D =10A		10.4	14	
Dynamic characteristics ⁴⁾						
Input Capacitance	C _{iss}	V _{DS} =15V,V _{GS} =0V,f =1MHz		1320		pF
Output Capacitance	C _{oss}			185		
Reverse Transfer Capacitance	C _{rss}			170		
Total Gate Charge	Q _g	V _{DS} =15V,V _{GS} =10V, I _D =15A		27		nC
Gate-Source Charge	Q _{gs}			5		
Gate-Drain Charge	Q _{gd}			7		
Turn-on delay time	t _{d(on)}	V _{DD} =15V,V _{GS} =10V, I _D =15A,R _{GEN} =2.2Ω		10.8		nS
Turn-on rise time	t _r			64.8		
Turn-off delay time	t _{d(off)}			22.5		
Turn-off fall time	t _f			3.7		
Source-Drain Diode characteristics						
Diode Forward Current	I _S				60	A
Diode Forward voltage	V _{SD}	V _{GS} =0V, I _S =15A			1.2	V
Reverse Recovery Time	t _{rr}	I _F =15A, di/dt =100A/μs		130		nS
Reverse Recovery Charge	Q _{rr}			157		nC

Notes:

- 1) Repetitive rating; pulse width limited by max. junction temperature.
- 2) $T_J=25^{\circ}\text{C}$, $V_G=10V$, $R_G=25\Omega$, $L=1\text{mH}$, $I_{AS}=11.9A$.
- 3) P_d is based on max. junction temperature, using junction-case thermal resistance.
- 4) Guaranteed by design, not subject to production.

Typical Characteristics

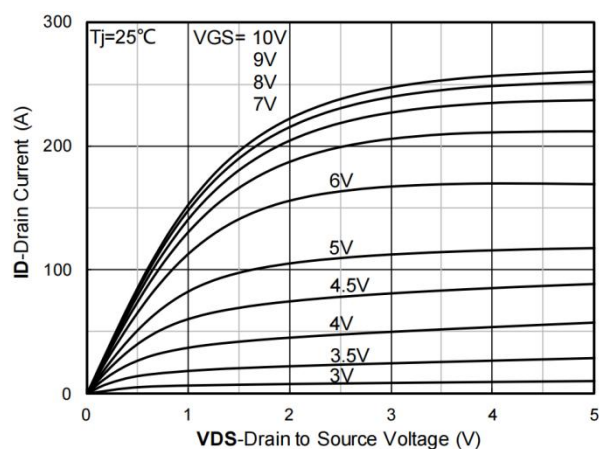


Figure 1. Output Characteristics

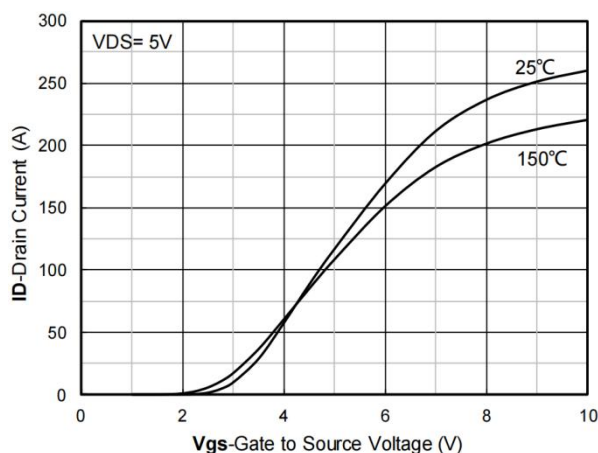


Figure 2. Transfer Characteristics

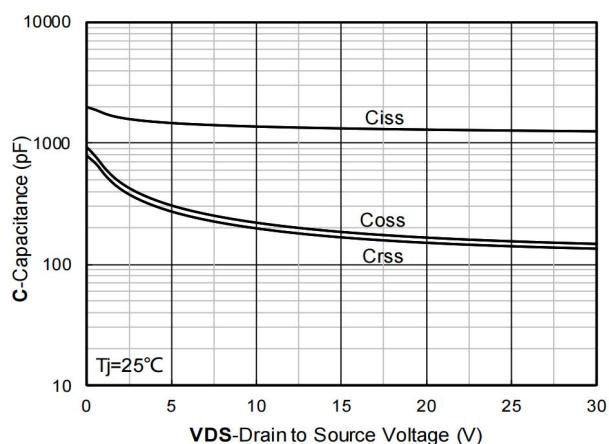


Figure 3. Capacitance Characteristics

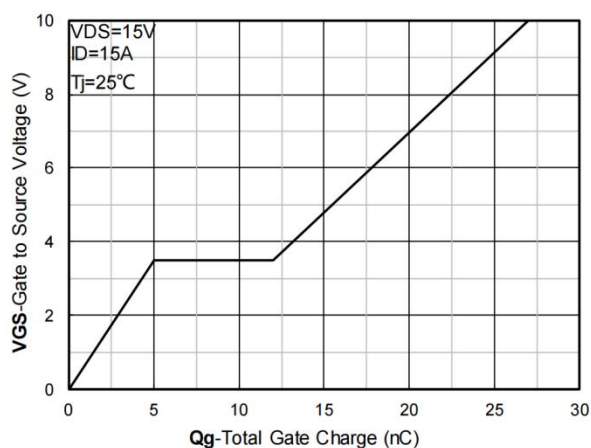


Figure 4. Gate Charge

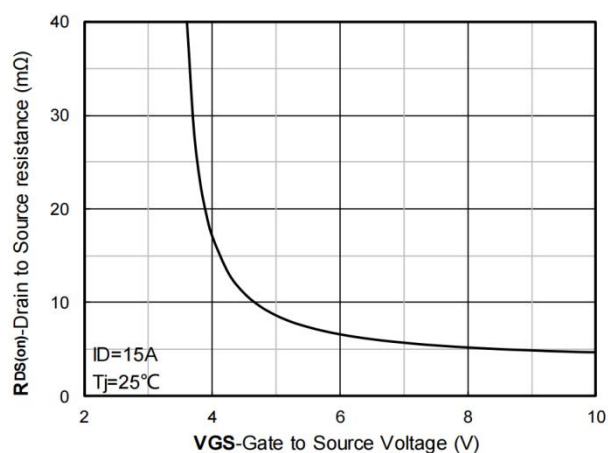


Figure 5. On-Resistance vs Gate to Source Voltage

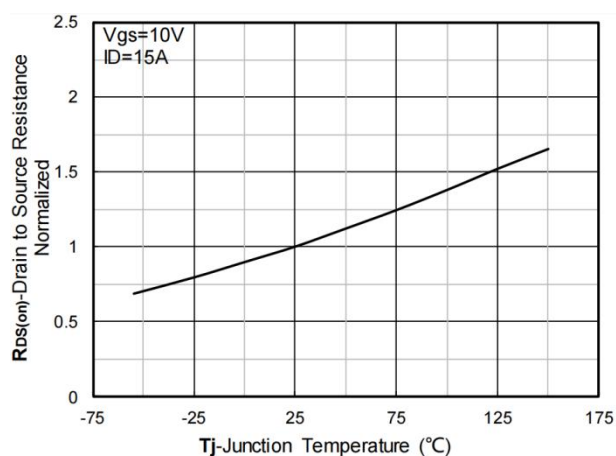


Figure 6. Normalized On-Resistance

Typical Characteristics

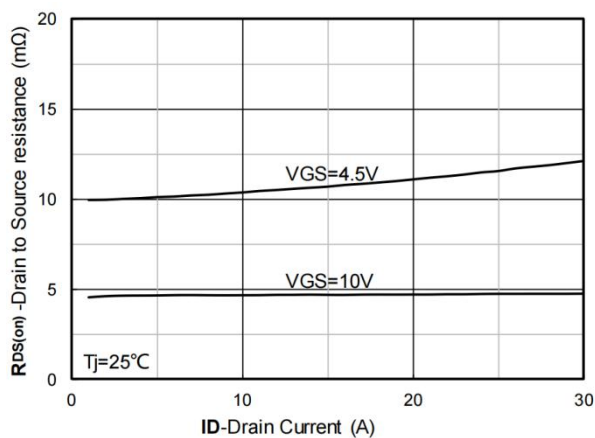


Figure 7. $R_{DS(on)}$ VS Drain Current

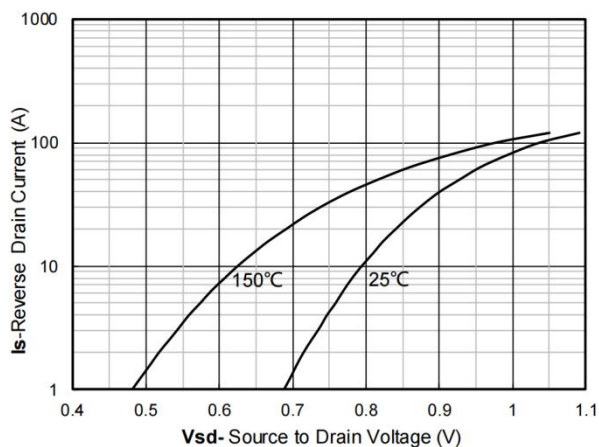


Figure 8. Forward characteristics of reverse diode

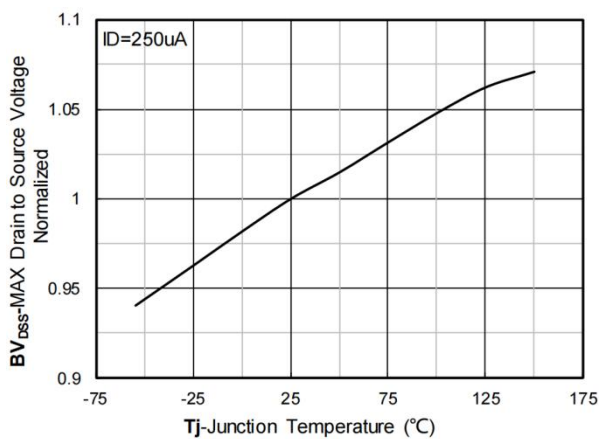


Figure 9. Normalized breakdown voltage

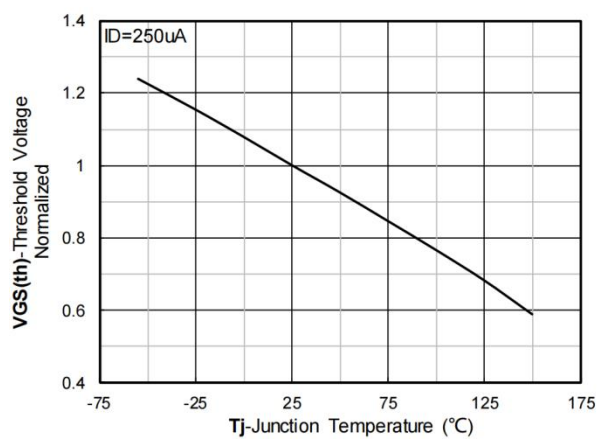


Figure 10. Normalized Threshold voltage

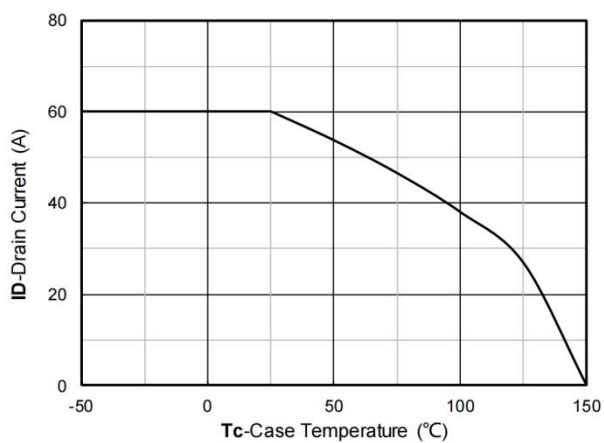


Figure 11. Current dissipation

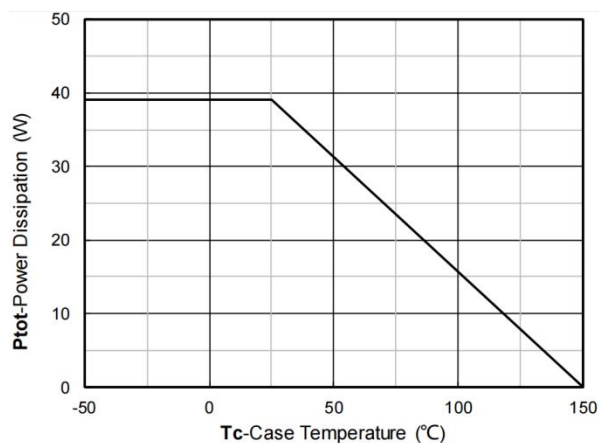


Figure 12. Power dissipation

Typical Characteristics

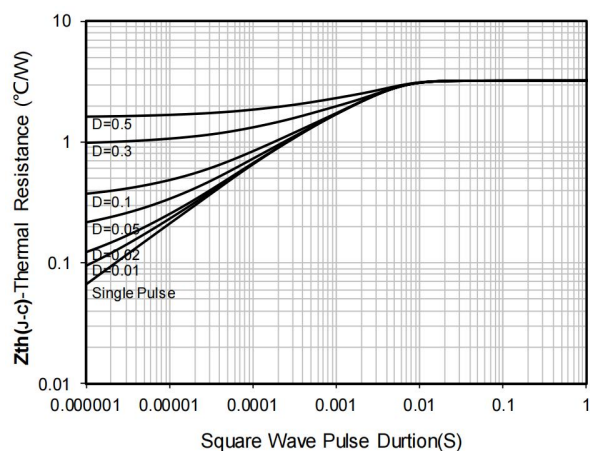


Figure 13. Maximum Transient Thermal Impedance

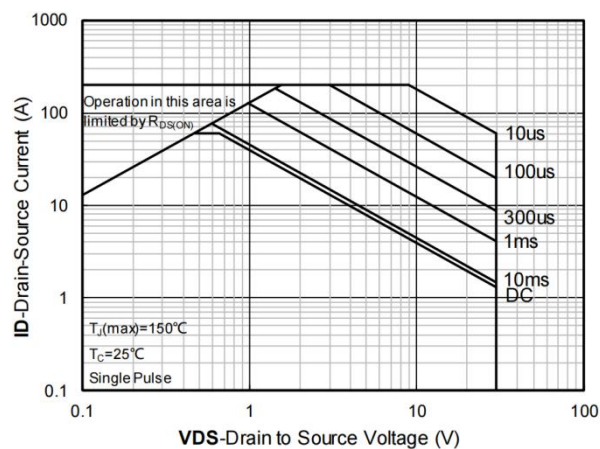
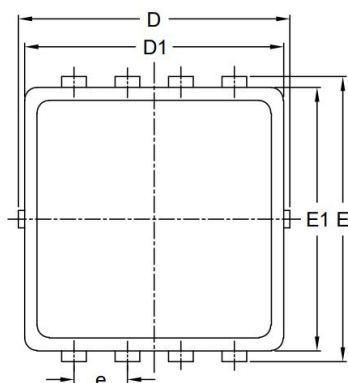
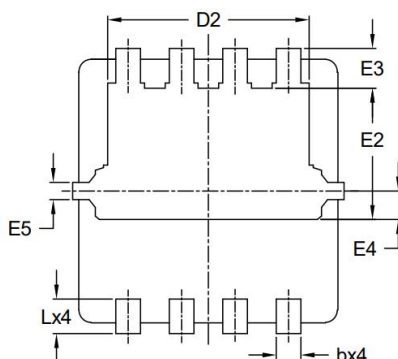


Figure 14. Safe Operation Area

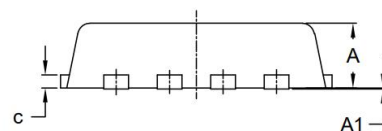
PDFN3.3*3.3-8L Package Information



TOP VIEW



BOTTOM VIEW



SIDE VIEW

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.850	0.028	0.033
A1	0.000	0.050	0.000	0.002
b	0.200	0.400	0.008	0.016
c	0.100	0.250	0.004	0.010
D	3.150	3.450	0.124	0.136
D1	3.000	3.300	0.118	0.130
D2	2.250	2.650	0.089	0.104
E	3.150	3.450	0.124	0.136
E1	2.900	3.200	0.114	0.126
E2	1.320	1.720	0.052	0.068
E3	0.280	0.650	0.011	0.026
E4	0.330 REF		0.013 REF	
E5	0.200 REF		0.008 REF	
e	0.650 BSC		0.026 BSC	
L	0.300	0.500	0.012	0.020